

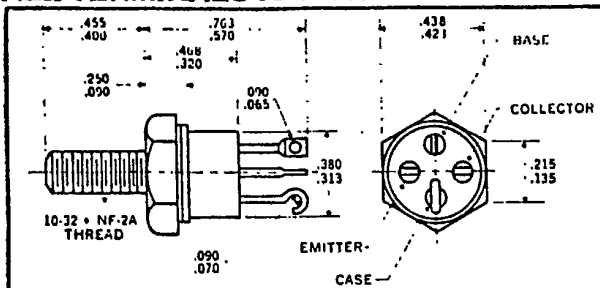
2N5659

10 AMP

HIGH SPEED NPN TRANSISTOR

120 VOLTS

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CASE STYLE Z**JEDEC TO-111****ALL TERMINALS ISOLATED FROM CASE****FEATURES**

- RADIATION TOLERANT
- FAST SWITCHING, 150 NSEC MAX t_{on}
- HIGH FREQUENCY, TYPICAL f_T 100 MHZ
- BVCEO 80 VOLTS MIN
- HIGH LINEAR GAIN, LOW SATURATION VOLTAGE
- 200°C OPERATING, GOLD EUTECTIC DIE ATTACH
- DESIGNED FOR COMPLEMENTARY USE WITH 2N6188 AND 2N6189

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	80	Volts
Collector - Base Voltage	V_{CBO}	120	Volts
Emitter - Base Voltage	V_{EBO}	7	Volts
Collector Current	I_C	10	Amps
Base Current	I_B	2	Amps
Total Device Dissipation @ $T_C = 100^\circ C$	P_D	30	Watts
Derate above 100 °C		300	mW/°C
Operating and Storage Temperature	T_j, T_{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.33	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
Collector - Emitter Breakdown Voltage* ($I_C = 100$ m Adc)	BV_{CEO}	80		Vdc
($I_C = 100$ m Adc, $R_{BE} = 10$ ohms)	BV_{CER}	120		Vdc
Collector - Base Breakdown Voltage ($I_C = 200$ u Adc)	BV_{CBO}	120		Vdc
Emitter - Base Breakdown Voltage ($I_E = 200$ u Adc)	BV_{EBO}	7		Vdc

Characteristics	Symbol	Min.	Max.	Unit
Collector Cutoff Current ($V_{CE} = 120$ Vdc)	I_{CES}		200	nAdc
Collector Cutoff Current ($V_{CE} = 80$ Vdc, $T_C = 150^\circ\text{C}$)	I_{CES}		100	μAdc
Emitter Cutoff Current ($V_{EB} = 7$ Vdc)	I_{EBO}		10	μAdc
DC Current Gain* ($I_C = 500$ mAdc, $V_{CE} = 2$ Vdc) ($I_C = 5$ Adc, $V_{CE} = 5$ Vdc) ($I_C = 10$ Adc, $V_{CE} = 5$ Vdc)	h_{FE}	40 50 30	250 150	
Collector - Emitter Saturation Voltage* ($I_C = 5$ Adc, $I_B = 500$ mAdc) ($I_C = 10$ Adc, $I_B = 1$ Adc)	$V_{CE(SAT)}$		0.5 1.0	Vdc
Base - Emitter Saturation Voltage* ($I_C = 5$ Adc, $I_B = 500$ mAdc) ($I_C = 10$ Adc, $I_B = 1$ Adc)	$V_{BE(SAT)}$		1.3 1.8	Vdc
Current - Gain - Bandwidth Product ($I_C = 500$ mAdc, $V_{CE} = 5$ Vdc, $f = 10$ MHz)	f_T	30		M Hz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, $f = 1$ MHz)	C_{ob}		150	pf
Delay Time Rise Time Storage Time Fall Time	t_d t_r t_s t_f		150	ns
($V_{CC} = 25$ Vdc, $I_C = 5$ Adc, (t_{on}) $I_{B1} = I_{B2} = 250$ mAdc, Base - Emitter clamp diode= 1N5802 or equivalent) (t_{off})			800	ns

*Pulse Test: Pulse width = 300 μs , Duty Cycle = 2%

TYPICAL OPERATING CURVES

